

ABSTRACT OF THE DISCLOSURE

An n-current blocking layer is formed by alternately stacking an n-first current blocking layer of a nitride based semiconductor containing Al or B and an n-second current blocking layer of a nitride based semiconductor containing In.

In a semiconductor laser device having a real refractive index guided structure, the mean refractive index of the n-current block layer is smaller than the refractive indices of a p-first cladding layer and a p-second cladding layer. In a semiconductor laser device having a loss guided structure, the mean band gap of the n-current blocking layer is substantially equal to or smaller than the mean band gap of an active layer.